

# UNR91A6G

## Silicon PNP epitaxial planar type

For digital circuits

■ Features

- Optimum for high-density mounting and downsizing of the equipment
- Contribute to low power consumption

■ Absolute Maximum Ratings  $T_a = 25^{\circ}\text{C}$

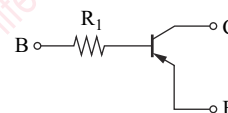
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	-50	V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	-50	V
Collector current	$I_{\text{C}}$	-80	mA
Total power dissipation	$P_{\text{T}}$	125	mW
Junction temperature	$T_{\text{j}}$	125	$^{\circ}\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to +125	$^{\circ}\text{C}$

■ Package

- Code  
SSMini3-F3
- Pin Name  
1: Base  
2: Emitter  
3: Collector

■ Marking Symbol: CN

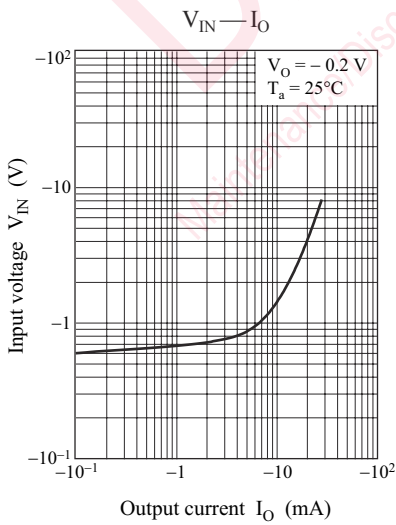
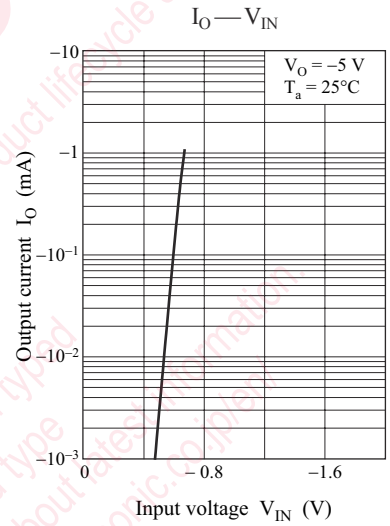
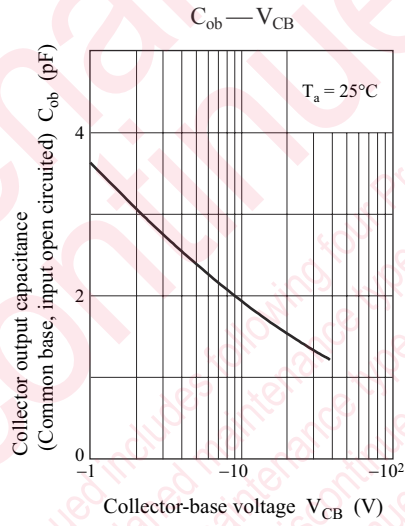
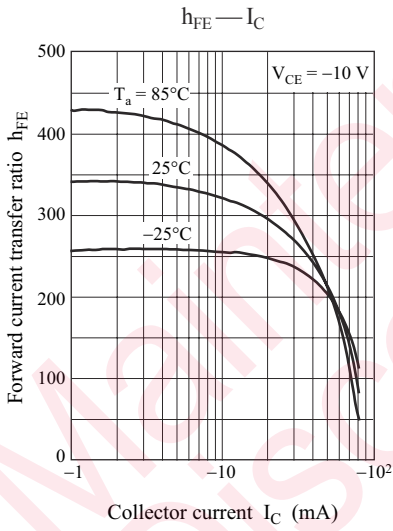
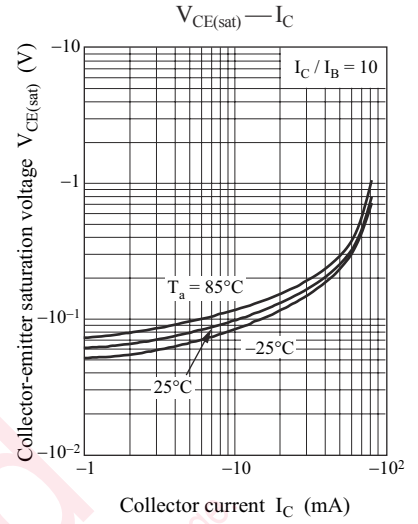
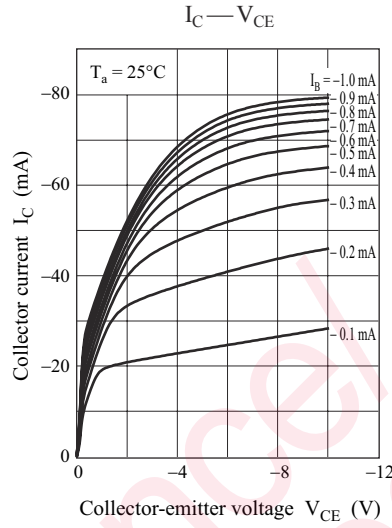
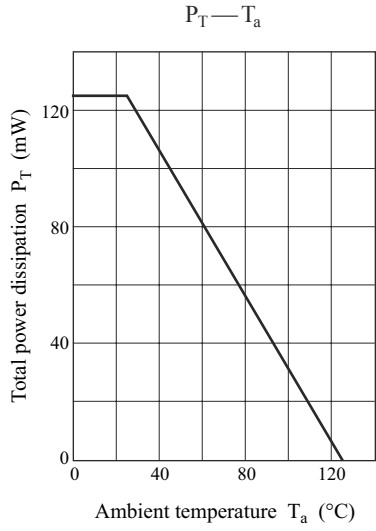
■ Internal Connection



■ Electrical Characteristics  $T_a = 25^{\circ}\text{C} \pm 3^{\circ}\text{C}$

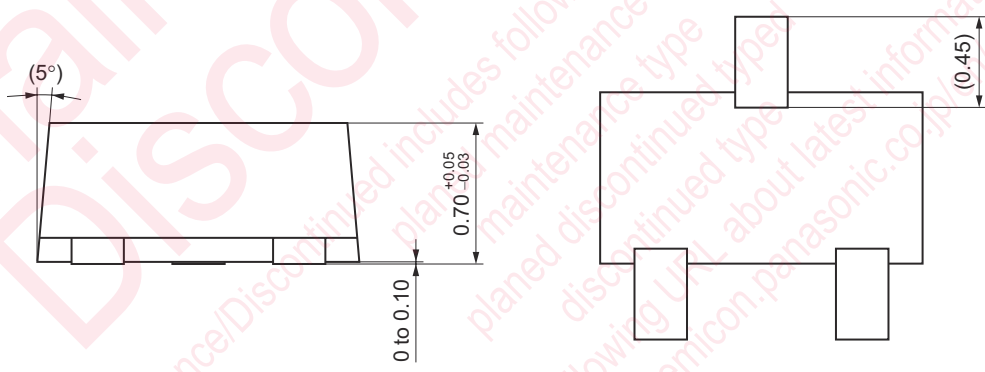
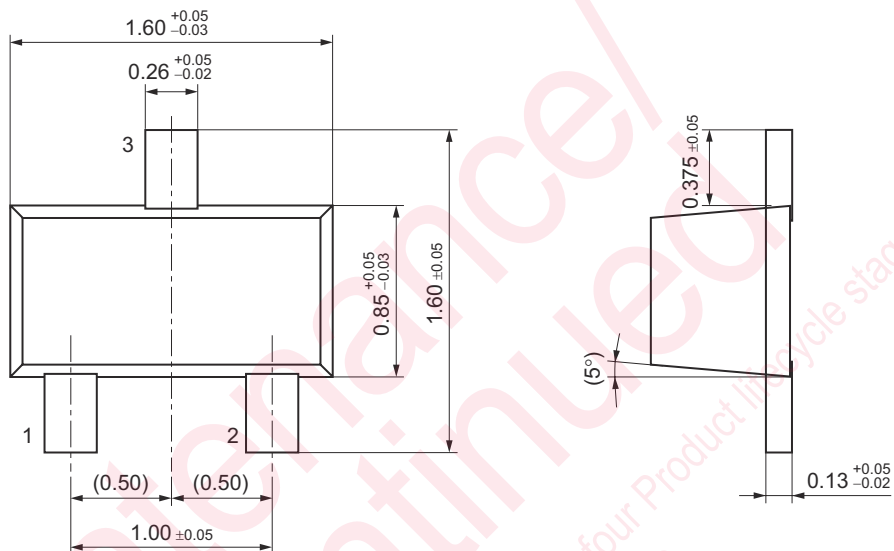
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	$I_{\text{C}} = -10 \mu\text{A}, I_{\text{E}} = 0$	-50			V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	$I_{\text{C}} = -2 \text{mA}, I_{\text{B}} = 0$	-50			V
Collector-base cutoff current (Emitter open)	$I_{\text{CBO}}$	$V_{\text{CB}} = -50 \text{V}, I_{\text{E}} = 0$			-0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{\text{CEO}}$	$V_{\text{CE}} = -50 \text{V}, I_{\text{B}} = 0$			-0.5	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{\text{EBO}}$	$V_{\text{EB}} = -6 \text{V}, I_{\text{C}} = 0$			-0.01	mA
Forward current transfer ratio	$h_{\text{FE}}$	$V_{\text{CE}} = -10 \text{V}, I_{\text{C}} = -5 \text{mA}$	160		460	—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -10 \text{mA}, I_{\text{B}} = -0.3 \text{mA}$			-0.25	V
Output voltage high-level	$V_{\text{OH}}$	$V_{\text{CC}} = -5 \text{V}, V_{\text{B}} = -0.5 \text{V}, R_{\text{L}} = 1 \text{k}\Omega$	-4.9			V
Output voltage low-level	$V_{\text{OL}}$	$V_{\text{CC}} = -5 \text{V}, V_{\text{B}} = -2.5 \text{V}, R_{\text{L}} = 1 \text{k}\Omega$			-0.2	V
Input resistance	$R_{\text{I}}$		-30%	4.7	+30%	$\text{k}\Omega$
Transition frequency	$f_{\text{T}}$	$V_{\text{CB}} = -10 \text{V}, I_{\text{E}} = 1 \text{mA}, f = 200 \text{MHz}$		80		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



SSMini3-F3

Unit: mm



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